

SENT BY: MCGINN& GIBB;

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YO998426DIV

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re patent application of

Chan et al.

Serial No. 10/051,562

Group Art Unit: 2822

Filed: January 18, 2002

Examiner: Novacek, Christy L.

or: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER BONDING TECHNIQUES

Commissioner For Patents  
Alexandria, VA 22313-1450

**AMENDMENT UNDER 37 C.F.R. §1.111**

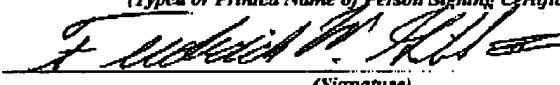
Sir:

In response to the Office Action mailed February 12, 2003, please amend the above-identified patent application as follows:

**IN THE CLAIMS:**

Please cancel claim 24 without prejudice or disclaimer.

Please amend the remaining claims as follows:

<b>CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)</b>				Docket No. <b>YO998-426DIV</b>
Applicant(s): Chan et al.				
Serial No. <b>10/051,562</b>	Filing Date <b>January 18, 2002</b>	Examiner <b>C. Novacek</b>	Group Art Unit <b>2822</b>	
<b>Invention: SELF-ALIGNED DOUBLE GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER BONDING TECHNIQUES</b>				
<p>I hereby certify that this <u>Amendment Under 37 CFR 1.111</u> <i>(Identify type of correspondence)</i></p> <p>is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. <u>703-872-9318</u>)</p> <p>on <u>May 9, 2003</u> <i>(Date)</i></p> <p style="text-align: right;"><u>Frederick W. Gibb, III</u> <i>(Typed or Printed Name of Person Signing Certificate)</i>  <i>(Signature)</i></p> <p><b>Note: Each paper must have its own certificate of mailing.</b></p> <p style="text-align: right;"><b>FAX RECEIVED</b> <b>MAY 09 2003</b> <b>TECHNOLOGY CENTER 2800</b></p>				